

ABSTRAT OF THE DISCLOSURE

There is provided a method of measuring defocusing when a semiconductor wafer is exposed to light. With the method, a resist is exposed to light by deviating a focus of the light by a given distance in relation to the semiconductor wafer with the resist applied thereto, and after development of the resist, resist patterns for measurement are formed. Based on respective lengths of the resist patterns for measurement, defocusing in relation to the resist is found.